

UT40N03T

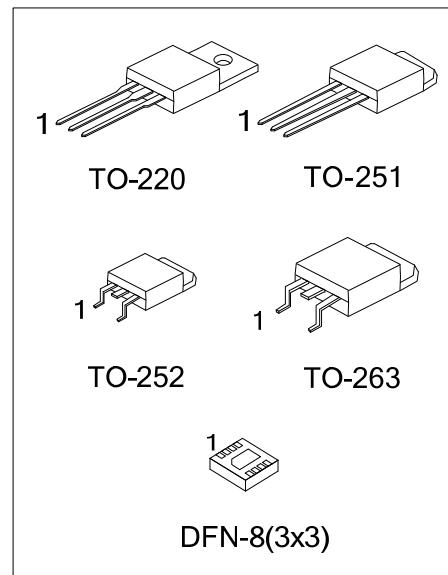
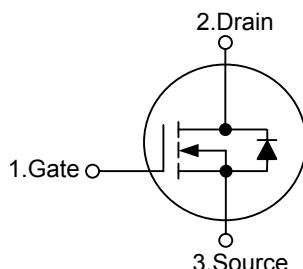
Power MOSFET

30V, 28A N-CHANNEL
ENHANCEMENT MODE
POWER MOSFET

■ FEATURES

- * $R_{DS(ON)} < 25m\Omega$ @ $V_{GS} = 10$ V
- * Low capacitance
- * Optimized gate charge
- * Fast switching capability
- * Avalanche energy specified

■ SYMBOL



■ ORDERING INFORMATION

Ordering Number		Package	Pin Assignment								Packing
Lead Free	Halogen Free		1	2	3	4	5	6	7	8	
UT40N03TL-TA3-T	UT40N03TG-TA3-T	TO-220	G	D	S	-	-	-	-	-	Tube
UT40N03TL-TM3-T	UT40N03TG-TM3-T	TO-251	G	D	S	-	-	-	-	-	Tube
UT40N03TL-TN3-R	UT40N03TG-TN3-R	TO-252	G	D	S	-	-	-	-	-	Tape Reel
UT40N03TL-TQ2-R	UT40N03TG-TQ2-R	TO-263	G	D	S	-	-	-	-	-	Tape Reel
UT40N03TL-TQ2-T	UT40N03TG-TQ2-T	TO-263	G	D	S	-	-	-	-	-	Tube
-	UT40N03TG-K08-3030-R	DFN-8(3x3)	S	S	S	G	D	D	D	D	Tape Reel

Note: Pin Assignment: G: Gate D: Drain S: Source

UT40N03TL-TN3-R	<p>(1)Packing Type</p> <p>(2)Package Type</p> <p>(3)Green Package</p>	<p>(1) R: Tape Reel, T: Tube</p> <p>(2) TA3: TO-220, TM3: TO-251, TN3:TO-252, TQ2: TO-263, K08-3030: DFN-8(3x3)</p> <p>(3) L: Lead Free, G: Halogen Free and Lead Free</p>
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■ MARKING

TO-220 / TO-251 / TO-252 / TO-263	DFN-8(3x3)

■ ABSOLUTE MAXIMUM RATINGS

PARAMETER		SYMBOL	RATINGS	UNIT
Drain-Source Voltage		V _{DSS}	30	V
Gate-Source Voltage		V _{GSS}	±25	V
Continuous Drain Current		I _D	28	A
Pulsed Drain Current		I _{DM}	95	A
Total Power Dissipation	TO-220/TO-263	P _D	31.25	W
	TO-251/ TO-252 DFN-8(3×3)		41	
Junction Temperature		T _J	+150	°C
Storage Temperature		T _{STG}	-55 ~ +150	°C

Note: Absolute maximum ratings are those values beyond which the device could be permanently damaged.

Absolute maximum ratings are stress ratings only and functional device operation is not implied.

■ THERMAL DATA

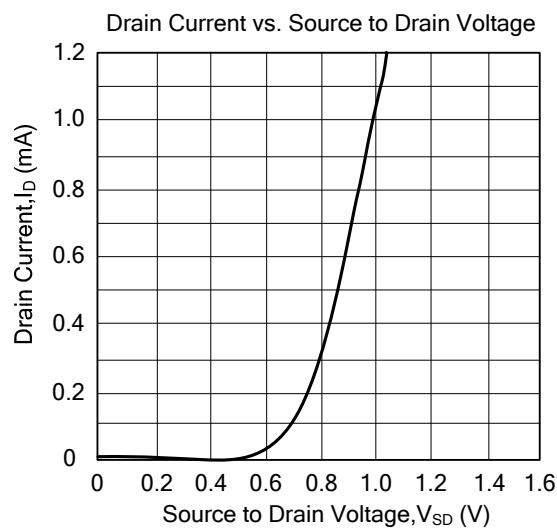
PARAMETER		SYMBOL	RATINGS	UNIT
Junction to Ambient	TO-220/TO-263	θ _{JA}	62	°C/W
	TO-251/ TO-252		60	
	DFN-8(3×3)		65	
Junction to Case	TO-220/TO-263	θ _{JC}	4	°C/W
	TO-251/ TO-252		3	
	DFN-8(3×3)			

■ ELECTRICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$, unless otherwise specified)

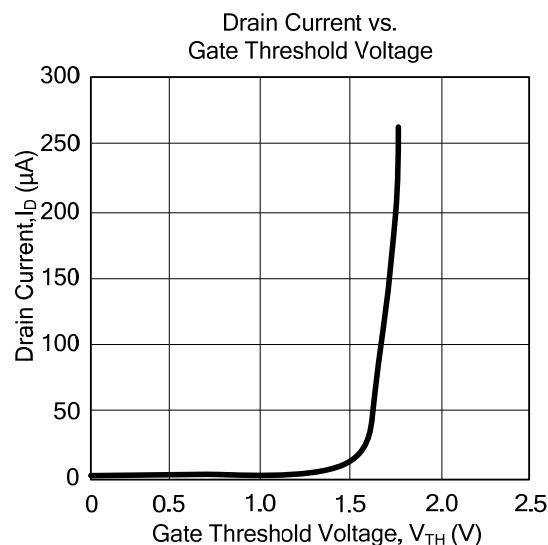
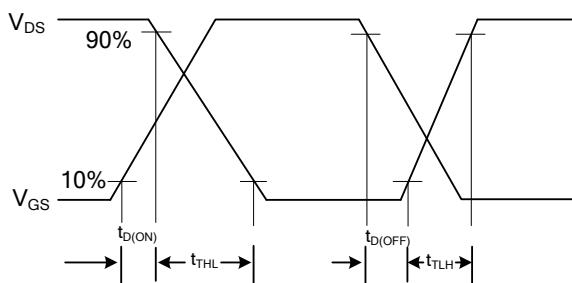
PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{\text{GS}} = 0 \text{ V}, I_{\text{D}} = 250 \mu\text{A}$	30			V
Drain-Source Leakage Current	I_{DSS}	$V_{\text{DS}} = 30 \text{ V}, V_{\text{GS}} = 0 \text{ V}, T_J = 25^\circ\text{C}$		1		μA
Gate-Source Leakage Current	I_{GSS}	$V_{\text{GS}} = \pm 25 \text{ V}$			± 100	nA
Breakdown Voltage Temperature Coefficient	$\Delta \text{BV}_{\text{DSS}}/\Delta T_J$	Reference to 25°C , $I_{\text{D}} = 1 \text{ mA}$	0.032			$\text{V}/^\circ\text{C}$
ON CHARACTERISTICS						
Gate-Threshold Voltage	$V_{\text{GS(TH)}}$	$V_{\text{DS}} = V_{\text{GS}}, I_{\text{D}} = 250 \mu\text{A}$	1		3	V
Drain-Source On-State Resistance	$R_{\text{DS(ON)}}$	$V_{\text{GS}} = 10 \text{ V}, I_{\text{D}} = 18 \text{ A}$		25		$\text{m}\Omega$
		$V_{\text{GS}} = 4.5 \text{ V}, I_{\text{D}} = 14 \text{ A}$		45		
DYNAMIC PARAMETERS						
Input Capacitance	C_{ISS}	$V_{\text{DS}} = 25 \text{ V}, V_{\text{GS}} = 0 \text{ V}, f = 1.0 \text{ MHz}$		655		pF
Output Capacitance	C_{OSS}			145		
Reverse Transfer Capacitance	C_{RSS}			95		
SWITCHING PARAMETERS						
Turn-ON Delay Time	$t_{\text{D(ON)}}$	$V_{\text{GS}} = 10 \text{ V}, V_{\text{DS}} = 15 \text{ V}, R_D = 0.83 \Omega, I_{\text{D}} = 18 \text{ A}, R_G = 3.3 \Omega$		6		ns
Turn-ON Rise Time	t_R			62		
Turn-OFF Delay Time	$t_{\text{D(OFF)}}$			16		
Turn-OFF Fall-Time	t_F			4.4		
Total Gate Charge	Q_G	$V_{\text{DS}} = 20 \text{ V}, V_{\text{GS}} = 4.5 \text{ V}, I_{\text{D}} = 18 \text{ A}$		8.8		nC
Gate-Source Charge	Q_{GS}			2.5		
Gate-Drain Charge	Q_{GD}			5.8		
SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS						
Drain-Source Diode Forward Voltage	V_{SD}	$I_{\text{S}} = 28 \text{ A}, V_{\text{GS}} = 0 \text{ V}$			1.3	V
Maximum Continuous Drain-Source Diode Forward Current	I_{S}	$V_D = V_G = 0 \text{ V}, V_S = 1.3 \text{ V}$			28	A
Maximum Pulsed Drain-Source Diode Forward Current	I_{SM}				95	A

Notes: 1. Pulse width limited by $T_{\text{J(MAX)}}$.2. Pulse width $\leq 300 \mu\text{s}$, duty cycle $\leq 2\%$.

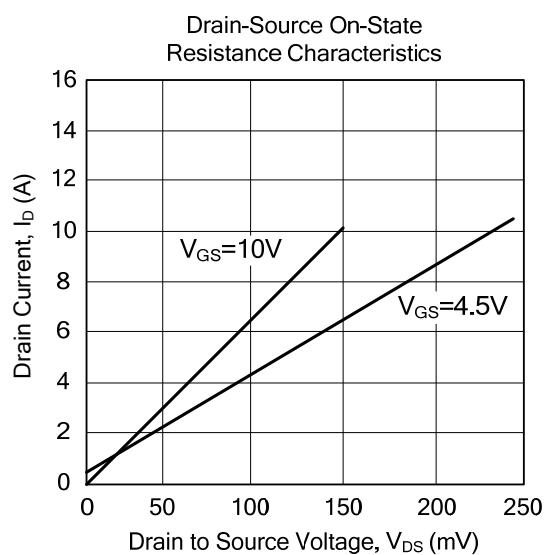
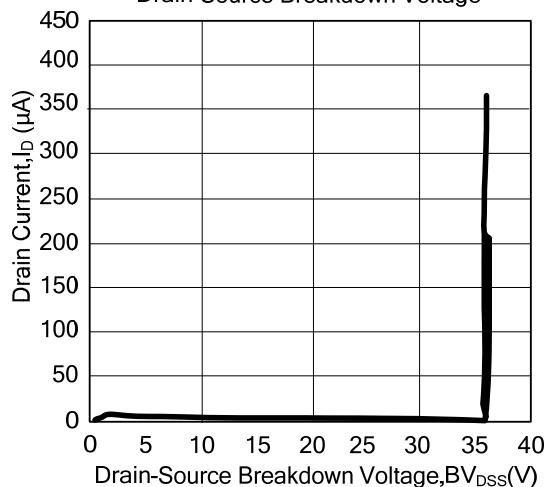
■ TYPICAL CHARACTERISTICS



Switching Time Waveforms



Drain Current vs.
Drain-Source Breakdown Voltage



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